

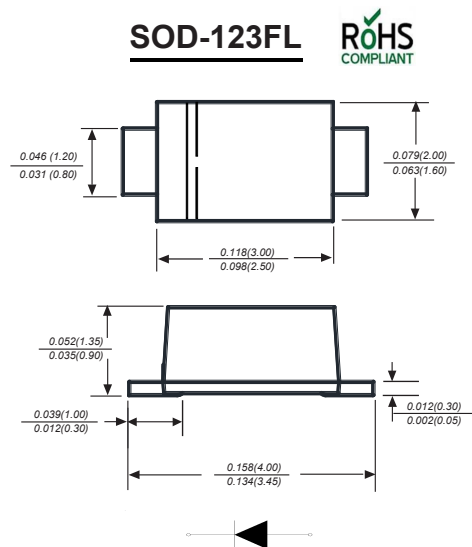
SURFACE MOUNT GENERAL PURPOSE SILICON RECTIFIER

Features

- ◆ Glass passivated device
- ◆ Ideal for surface mouted applications
- ◆ Low reverse leakage
- ◆ Metallurgically bonded construction
- ◆ High temperature soldering guaranteed:
- ◆ 260°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

Mechanical Data

Case: JEDEC UOD-123FL molded plastic body
 Terminals: Solderable per MIL-STD-750, Method 2026A
 Polarity: Polarity symbol marking on body
 Mounting Position: Any
 Weight: 0.0053ounce, 0.015grams



Dimensions in inches and (millimeters)

Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	SYMBOLS	SM4001PL	SM4002PL	SM4003PL	SM4004PL	SM4005PL	SM4006PL	SM4007PL	UNITS
Marking Code		A1	A2	A3	A4	A5	A6	A7	
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current at TL (NOTE 1)	$I_{(AV)}$	1.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	25							A
Maximum instantaneous forward voltage at 1.0A	V_F	1.1							V
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=125^\circ\text{C}$	I_R	10 50							μA
Typical junction capacitance (NOTE 2)	C_J	4							pF
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$	180							$^\circ\text{C}/\text{W}$
Operating junction temperature range	T_J	-55 to +150							$^\circ\text{C}$
Storage temperature range	T_{STG}	-55 to +150							$^\circ\text{C}$

Note: 1. Averaged over any 20ms period.

2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

3. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted

Typical Characteristics

Fig.1 Forward Current Derating Curve

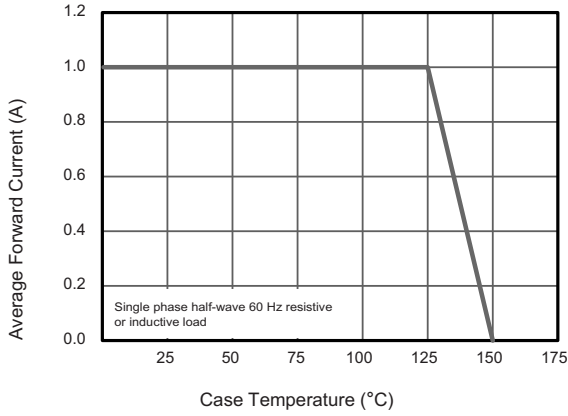


Fig.2 Typical Instaneous Reverse Characteristics

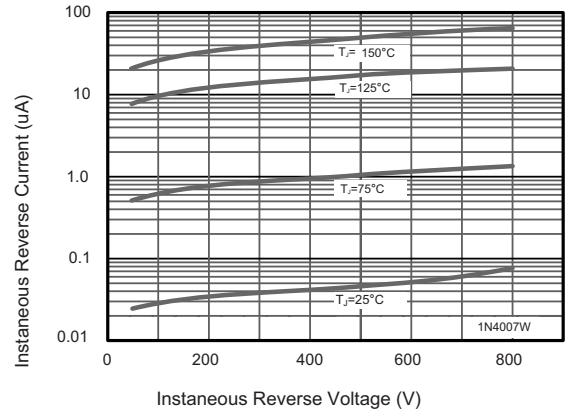


Fig.3 Typical Forward Characteristic

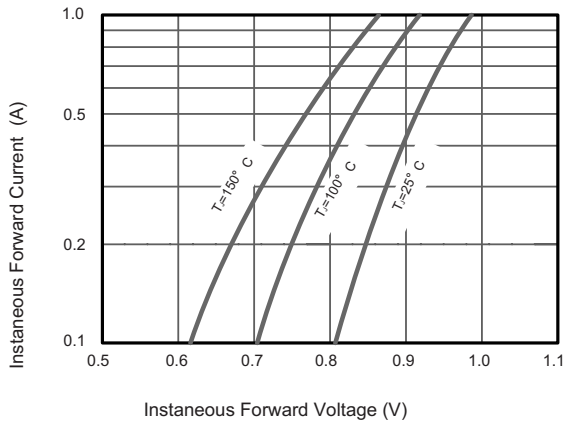


Fig.4 Typical Junction Capacitance

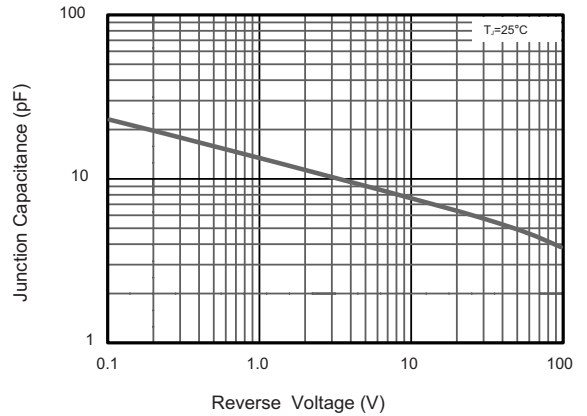
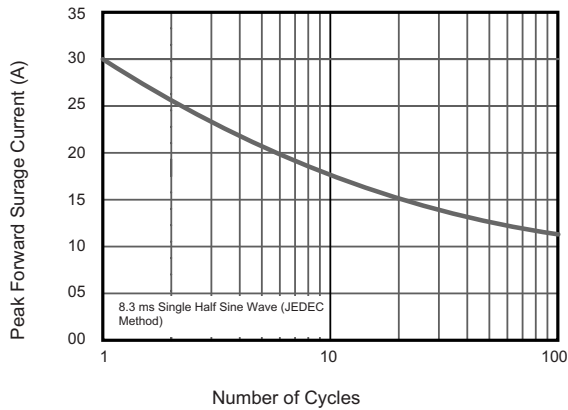
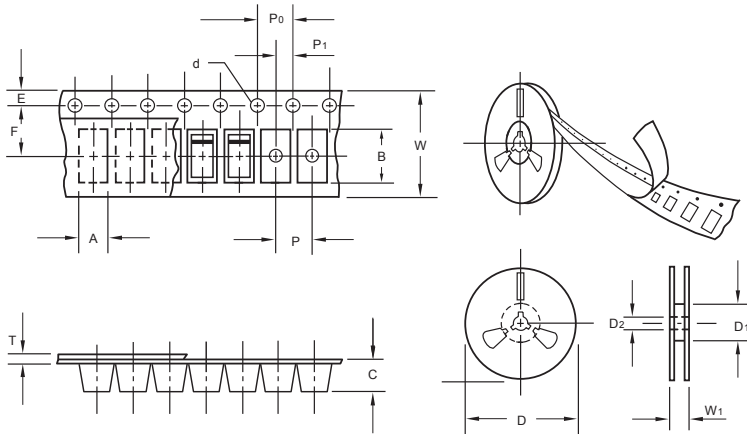


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current



The curve above is for reference only.

Packing information



unit:mm

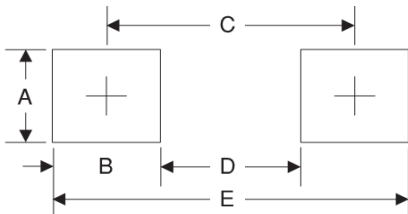
Item	Symbol	Tolerance	SOD-123FL
Carrier width	A	0.1	2.1
Carrier length	B	0.1	4.0
Carrier depth	C	0.1	1.60
Sprocket hole	d	0.05	1.55
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D ₁	min	50.0
Feed hole diameter	D ₂	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P ₀	0.1	4.00
Embossment center	P ₁	0.1	2.00
Overall tape thickness	T	0.1	0.25
Tape width	W	0.3	8.15
Reel width	W ₁	1.0	10.5

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOD-123FL	7"	3,000	4.0	45,000	190*190*190	178	400*400*220	180,000	9.0

Suggested Pad Layout



Symbol	Unit (mm)	Unit (inch)
A	1.2	0.047
B	1.2	0.047
C	3.2	0.126
D	2	0.079
E	4.4	0.173

Important Notice and Disclaimer

Microdiode Semiconductor(Shenzhen) reserves the right to make changes to this document and its products and specifications at any time without notice. Customers should obtain and confirm the latest product information and specifications before final design, purchase or use.

Microdiode Semiconductor(Shenzhen) makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Microdiode Semiconductor(Shenzhen) assume any liability for application assistance or customer product design. Microdiode Semiconductor(Shenzhen) does not warrant or accept any liability with products which are purchased or used for any unintended or unauthorized application.

No license is granted by implication or otherwise under any intellectual property rights of Microdiode Semiconductor(Shenzhen).

Microdiode Semiconductor(Shenzhen) products are not authorized for use as critical components in life support devices or systems without express written approval of Microdiode Semiconductor(Shenzhen).